



DCR3640W52

Phase Control Thyristor

Replaces DS5819-4 DS5819-5 June 2022 (LN41816)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions	
		Tvj = -40°C to 125°C,	
DCR3640W52*	5200	IDRM = IRRM = 300mA,	
DCR3640W50	5000	VDRM, VRRM tp = 10ms	
DCR3640W48	4800	VDSM & VRSM =	
DCR3640W46	4600	VDRM & VRRM + 100V	
		respectively	

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR3640W52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

\mathbf{V}_{DRM}	5200V
I _{T(AV)}	3560A
Ітѕм	49000A
dV/dt*	1500V/µs
dl/dt	400A/μs

^{*} Higher dV/dt selections are available on request

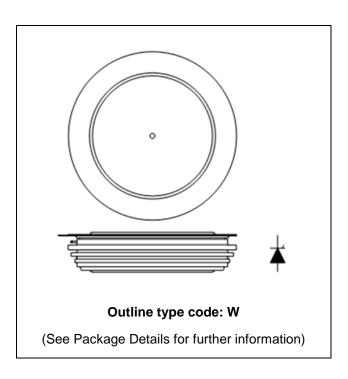


Fig. 1 Package outline

www.dynexsemi.com 1/10

^{*5000}V @ -40°C, 5200V @ 0°C



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
IT(AV)	Mean on-state current	Half wave resistive load	3560	А
IT(RMS)	RMS value	-	5590	А
lτ	Continuous (direct) on-state current	-	5250	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	49.0	kA
l²t	I2t for fusing	V _R = 0	12.0	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
		Double side cooled	DC	-	6.3	°C/kW
Rth(j-c)	Thermal resistance - junction to case	Cingle side spaled	Anode DC	-	11.2	°C/kW
	Single side cooled	Cathode DC	-	14.5	°C/kW	
D ate 13	Thermal registance, each to heatainly	Clamping force 76kN	Double side	-	1.4	°C/kW
Ktn(c-n)	Rth(c-h) Thermal resistance - case to heatsink	(with mounting compound)	Single side	-	2.8	°C/kW
Tvj	Virtual junction temperature	Blocking Vdrm/ Vrrm		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			68	84	kN

www.dynexsemi.com 2/10



DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Condition	ns	Min.	Max.	Units
IRRM/IDRM	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	;	-	300	mA
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		1.50	1.75	٧
dV/dt	Max. linear rate of rise of off-state voltage	То 67% VdRM, Tj = 125°C, g	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)} Gate source 30V, 10Ω	Repetitive 50Hz	-	200	A/µs
ui/at	ivate of fise of off-state current	tr < 0.5µs, Tj = 125°C	Non-repetitive	-	400	A/µs
V	Threshold voltage - Low level	500A to 2800A at Tcase = 1	-	0.87	V	
V T(TO)	Threshold voltage - High level	2800A to 7000A at Tcase = 125°C		-	1.09	٧
_	On-state slope resistance - low level	500A to 2800A at Tcase = 125°C		-	0.25	mΩ
ľτ	On-state slope resistance - High level	2800A to 7000A at Tcase = 125°C		-	0.17	mΩ
tgd	Delay time	$V_D = 67\% \ V_{DRM}$, gate source 30V, 10Ω $t_T = 0.5 \mu s$, $T_j = 25 ^{\circ} C$		-	3	μs
tq	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, $dI/dt = 1$ A/ μ s, $dV_{DR}/dt = 20$ V/ μ s linear		400	750	μs
Qs	Stored charge	Iτ = 2000A, Tj = 125°C, dI/dt = 1A/μs VR(peak) ~ 3100V, VRM ~ 2100V		2700	6330	μC
IRR	Reverse recovery current			45	69	А
lι	Latching current	Tj = 25°C, VD = 5V		-	3	А
Ін	Holding current	Tj = 25°C, Rg-к = ∞, Iтм = 50	0A, Ιτ = 5A	-	300	mA

www.dynexsemi.com 3/10



GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
V GD	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
Ідт	Gate trigger current	VDRM = 5V, Tcase = 25°C	400	mA
IGD	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	10	mA

CURVES

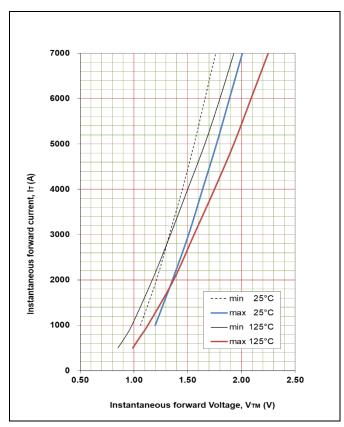


Fig. 2 Maximum & minimum on-state characteristics

VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.706988

B = -0.002428

C = 0.000090

D = 0.011102

These values are valid for T_j = 125°C for I_T 500A to 7000A

www.dynexsemi.com 4/10



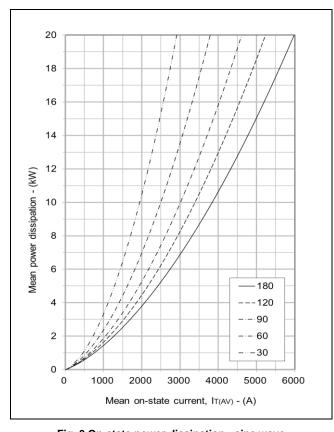


Fig. 3 On-state power dissipation - sine wave

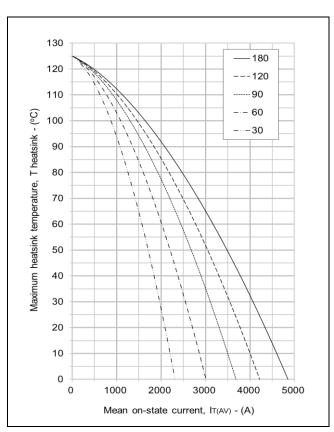


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

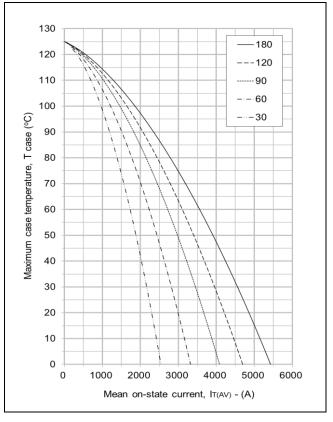


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

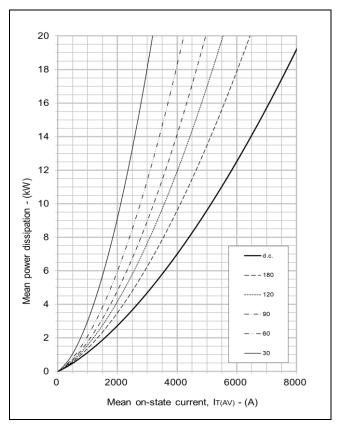


Fig. 6 On-state power dissipation - rectangular wave

www.dynexsemi.com 5/10



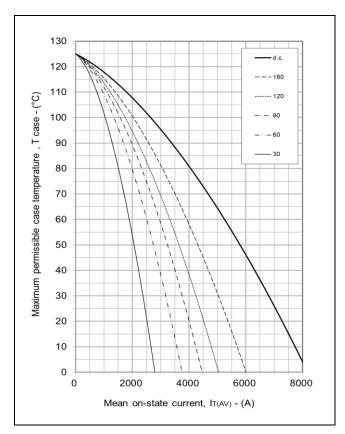
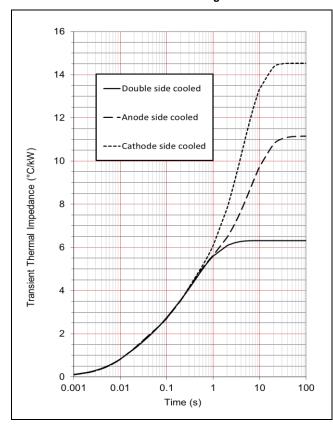


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



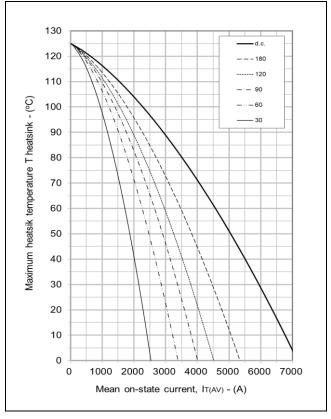


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	0.882	1.299	2.805	1.331
cooled	Ti(s)	0.011	0.058	0.358	1.129
Anode side cooled	Ri(°C/kW)	1.520	3.240	5.762	0.631
	Ti(s)	0.017	0.242	6.013	15.364
Cathode side	Ri(°C/kW)	1.411	2.467	6.745	3.905
cooled	Ti(s)	0.016	0.179	3.620	6.196

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance R $_{\text{th}(j-c)}$ when the device operates at conduction angles other than d.c.

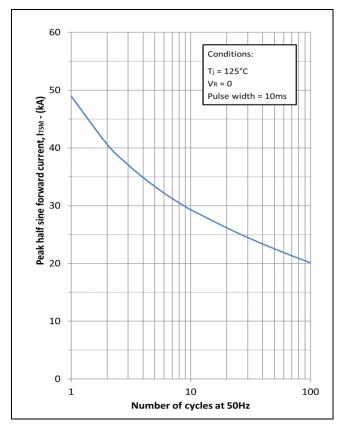
Double side cooling				Anode Side Cooling			
	ΔZ_{th} (z)				ΔZ_{i}	h (Z)	
θ°	sine.	rect.		θ°	sine.	re ct	
180	1.00	0.67		180	0.94	0.64	
120	1.16	0.97		120	1.08	0.91	
90	1.33	1.13		90	1.23	1.06	
60	1.48	1.31		60	1.37	1.22	
30	1.61	1.51		30	1.47	1.38	
1.5	1 66	1.01	1	15	1.50	4.47	

ooling	Cathode Sided Cooling				
(z)		$\Delta Z_{th}(z)$			
rect.	θ°	sine.	rect.		
0.64	180	0.95	0.65		
0.91	120	1.09	0.92		
1.06	90	1.25	1.07		
1.22	60	1.38	1.23		
1.38	30	1.49	1.40		
1.47	15	1.54	1.49		

Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

www.dynexsemi.com 6/10





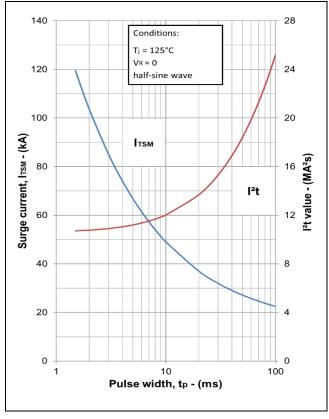


Fig. 10 Multi-cycle surge current

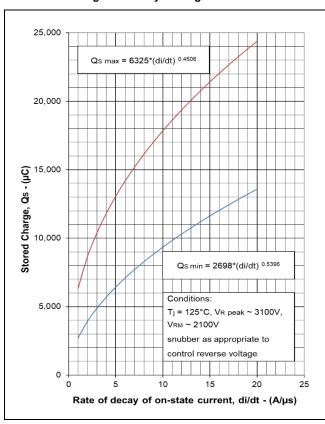


Fig. 12 Reverse recovery charge

Fig. 11 Single-cycle surge current

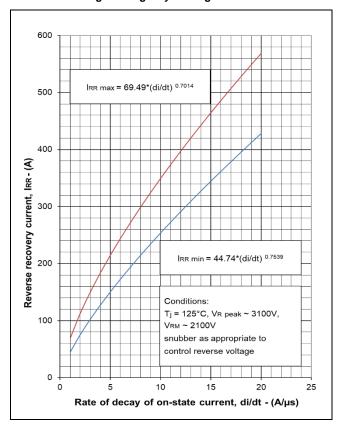


Fig. 13 Reverse recovery current

www.dynexsemi.com 7/10



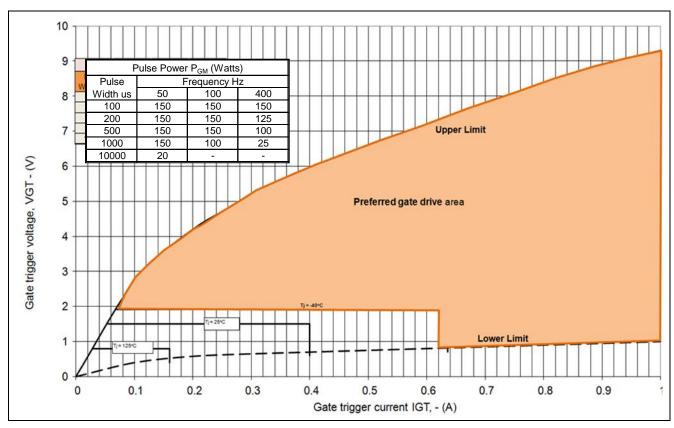


Fig. 14 Gate characteristics

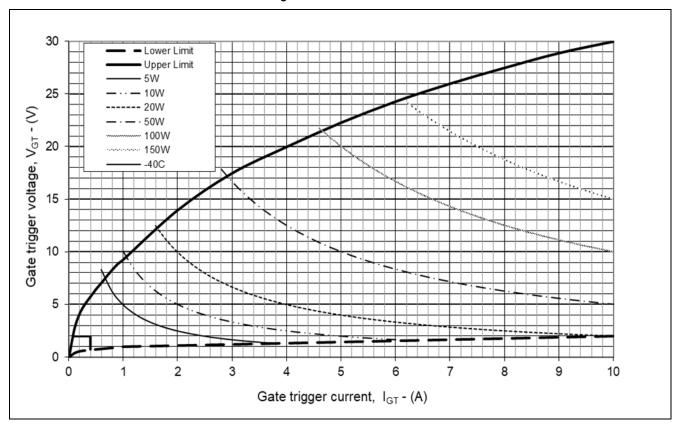


Fig. 15 Gate characteristics

www.dynexsemi.com 8/10



PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

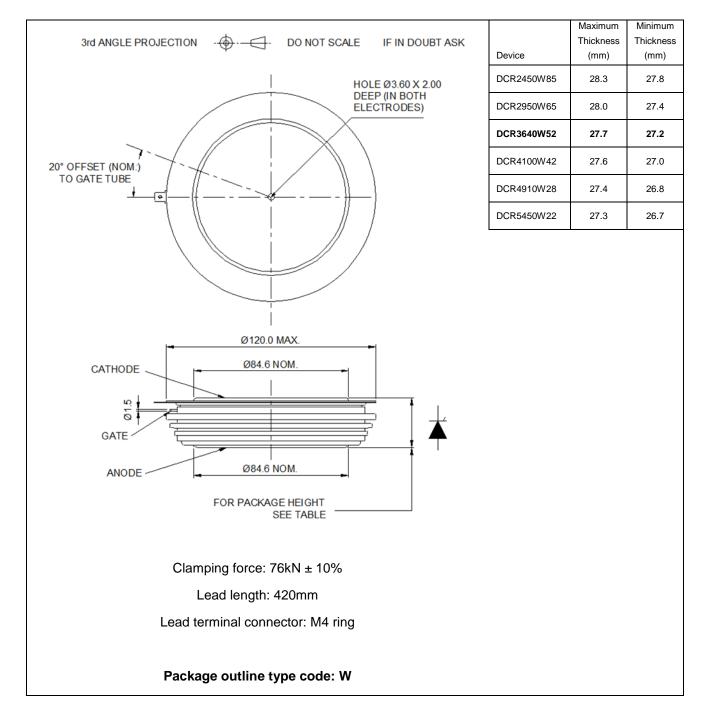


Fig. 16 Package outline

www.dynexsemi.com 9/10



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www.dynexsemi.com 10/10